描述 / Descriptions

TO-126(R)塑封封装 NPN 半导体三极管。Silicon NPN transistor in a TO-126(R) Plastic Package.

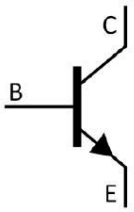
特征 / Features

耐压高，快速转换。
High Voltage Capability High Speed Switching.

用途 / Applications

主要用于节能灯、日光灯电子镇流器及其它开关、振荡电路。
High frequency electronic lighting ballast applications,converters, inverters, switching regulators, etc.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning

PIN1：Base　　PIN 2：Collector　　PIN 3： Emitter

放大及印章代码 / h_{FE} Classifications & Marking

见印章说明　　See Marking Instructions

极限参数 / Absolute Maximum Ratings(Ta=25℃)

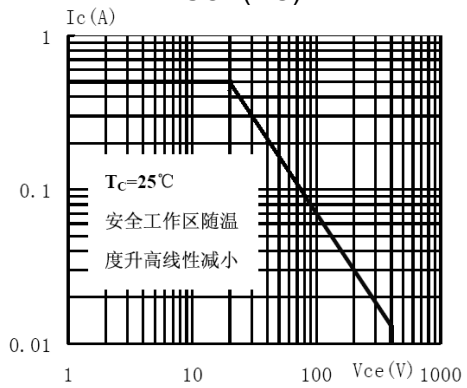
参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	600	V
Collector to Emitter Voltage	V_{CEO}	400	V
Emitter to Base Voltage	V_{EBO}	9.0	V
Collector Current - Continuous	I_C	0.8	A
Collector Power Dissipation	P_C	1.25	W
Collector Power Dissipation	P_C(Tc=25℃)	20	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

电性能参数 / Electrical Characteristics(Ta=25℃)

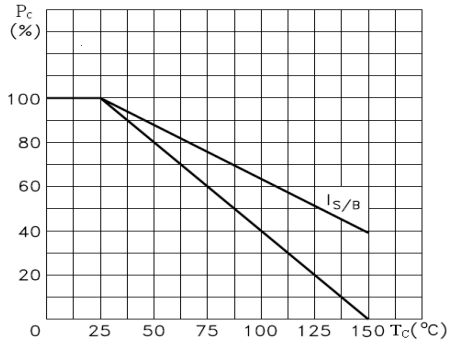
参数 Parameter	符号 Symbol	测试条件 Test Conditions		最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=1mA	I_E=0	600			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=10mA	I_B=0	400			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=1mA	I_C=0	9.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=600V	I_E=0			0.1	mA
Collector cut-off current	I_{CEO}	V_{CE}=400V	I_B=0			0.1	mA
Emitter Base Cut-Off Current	I_{EBO}	V_{EB}=9.0V	I_C=0			0.1	mA
DC Current Gain	h_{FE}	V_{CE}=5.0V	I_C=200mA	10		40	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=200mA	I_B=40mA			0.5	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=200mA	I_B=40mA			1.2	V
Transition Frequency	f_T	V_{CE}=10V f=1.0MHz	I_C=50mA	5.0			MHz
Fall time	t_f	V_{CE}=5V (UI9600)	I_C=100mA			0.6	μs
Storage time	ts					4.0	μs

电参数曲线图 / Electrical Characteristic Curve

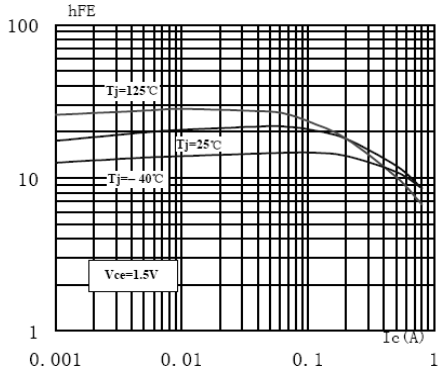
SOA(DC)



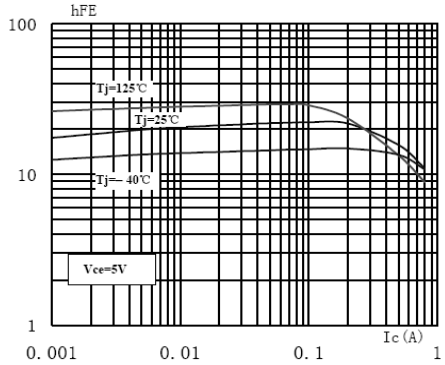
P_C-T_C



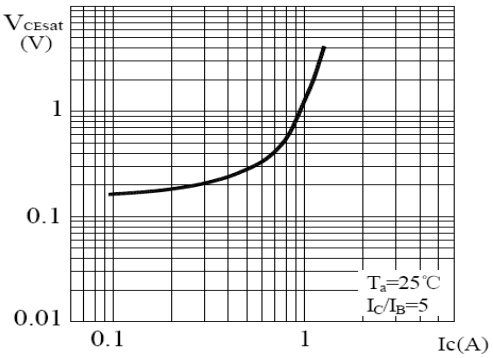
h_{FE}-Ic



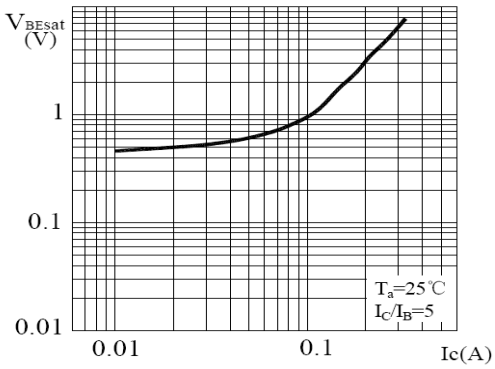
h_{FE}-Ic



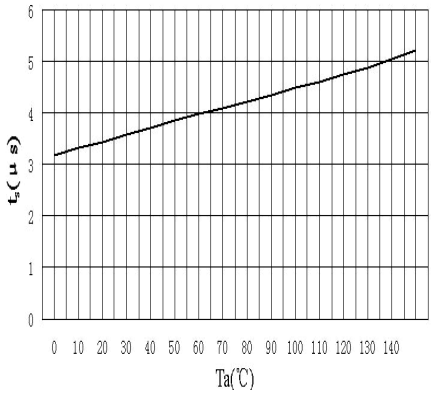
Vces-I_C



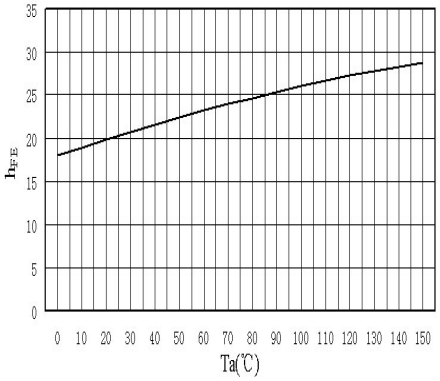
Vbes-I_C



t_S-Ta

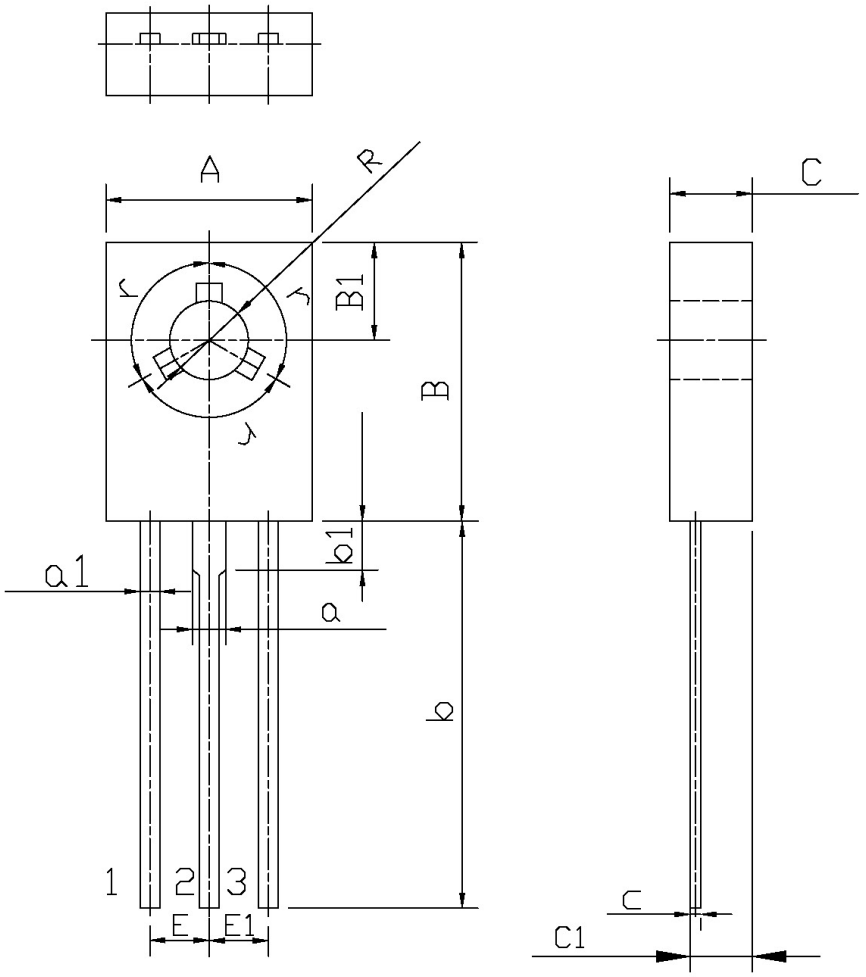


h_{FE}-Ta



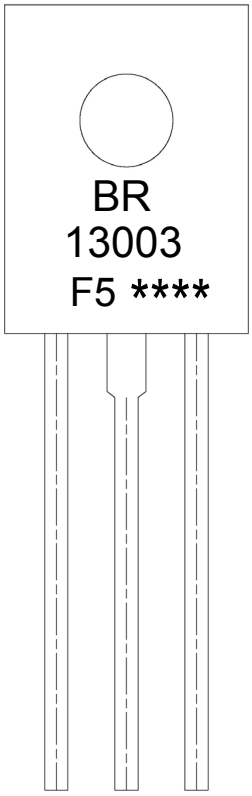
外形尺寸图 / Package Dimensions

TO-126(R)　　单位：mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	7.4	7.8	a1	0.66	0.86
B	10.6	11.0	E	2.1	2.5
B1	3.8	4.2	C	2.55	2.85
R	2.9	3.3	C1	1.60	1.80
b	14	16	c	0.3	0.6
b1	1.9		a	1.37	
E1	2.1	2.5	r	120°	

印章说明 / Marking Instructions



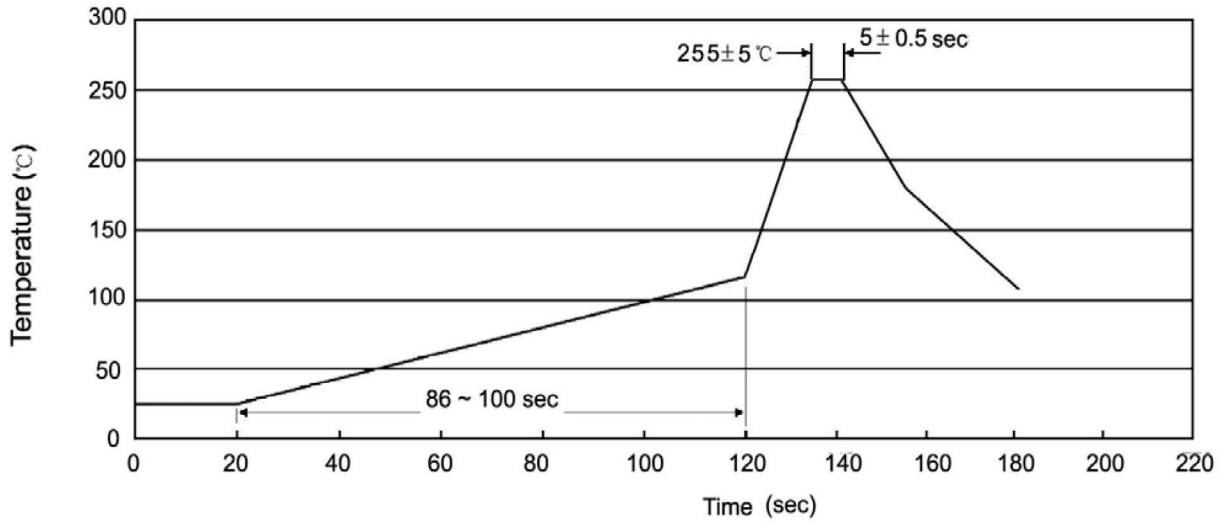
说明：

BR：	为公司代码
13003：	为型号代码
F5:	为规格代码
****：	为生产批号代码，随生产批号变化。

Note:

BR:	Company Code
13003:	Product Type Code.
F5:	Specification Code.
****:	Lot No. Code, code change with Lot No.

波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)



说明：

1、预热温度 25～150℃，时间 60～90sec;

2、峰值温度 255±5℃，时间持续为 5±0.5sec;

3、焊接制程冷却速度为 2～10℃/sec.

Note:

1.Preheating:25~150℃, Time:60~90sec.

2.Peak Temp.:255±5℃, Duration:5±0.5sec.

3. Cooling Speed: 2~10℃/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：270±5℃　　时间：10±1 sec.　　Temp.:270±5℃　　Time:10±1 sec

包装规格 / Packaging SPEC.

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-126/F	500	6	3,000	5	15,000	135×190	237×172×102	560×245×195

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-126/F	65	26	1,690	5	8,450	532×31×5.6	555×164×50	575×290×180

使用说明 / Notices